# Low-Voltage, Sub-Ohm, SPDT Analog Switch 

## FEATURES

- Low Voltage Operation ( 1.6 V to 3.6 V )
- Low On-Resistance - ros(on): $0.44 \Omega$ Typ.
- Fast Switching - ton $: 25 \mathrm{~ns}, \mathrm{t}_{\mathrm{OFF}}: 14 \mathrm{~ns}$
- Low Leakage
- TTL/CMOS Compatible
- 6-Pin SC-70 Package


## BENEFITS

- Reduced Power Consumption
- Simple Logic Interface
- High Accuracy
- Reduce Board Space


## APPLICATIONS

- Cellular Phones
- Communication Systems
- Portable Test Equipment
- Battery Operated Systems
- Sample and Hold Circuits


## DESCRIPTION

The DG2711 is a sub-ohm single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (ton: $25 \mathrm{~ns}, \mathrm{t}_{\text {OFF: }} 14 \mathrm{~ns}$ ), low on-resistance ( $r_{\mathrm{DS}(\mathrm{on})}: 0.44 \Omega$ ) and small physical size (SC70), the DG2711 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2711 is built on Vishay Siliconix's low voltage submicron CMOS process. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG2711.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead $(\mathrm{Pb})$-free device terminations. For analog switching products manufactured with $100 \%$ matte tin device terminations, the lead ( Pb )-free "-E3" suffix is being used as a designator.

## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



| TRUTH TABLE |  |  |
| :---: | :---: | :---: |
| Logic | NC | NO |
| 0 | ON | OFF |
| 1 | OFF | ON |


| ORDERING INFORMATION |  |  |
| :---: | :---: | :---: |
| Temp Range | Package | Part Number |
| -40 to $85^{\circ} \mathrm{C}$ | SC70-6 | DG2711DL-T1-E3 |

## ABSOLUTE MAXIMUM RATINGS

| Reference to GND |  |
| :---: | :---: |
| V+ | -0.3 to +4 V |
| IN, COM, NC, NOª | -0.3 to (V++0.3 V) |
| Continuous Current (NO, NC and COM Pins) | $\pm 200 \mathrm{~mA}$ |
| Peak Current | . $\pm 300 \mathrm{~mA}$ |
| (Pulsed at $1 \mathrm{~ms}, 10 \%$ duty cycle) |  |
| Storage Temperature (D Suffix) | . . . 65 to $150^{\circ} \mathrm{C}$ |

Power Dissipation (Packages) ${ }^{\text {b }}$
6-Pin SO70c . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . . 250 mW

## Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate $3.1 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $70^{\circ} \mathrm{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| SPECIFICATIONS (V+ = 1.8 V) |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Parameter | Symbol | Test Conditions Otherwise Unless Specified$\mathrm{V}_{+}=1.8 \mathrm{~V}, \pm 10 \%, \mathrm{~V}_{\mathrm{IN}}=0.4 \text { or } 1.0 \mathrm{Ve}$ | Temp ${ }^{\text {a }}$ | Limits <br> -40 to $85^{\circ} \mathrm{C}$ |  |  | Unit |
|  |  |  |  | Min ${ }^{\text {b }}$ | Typ ${ }^{\text {c }}$ | Max ${ }^{\text {b }}$ |  |
| Analog Switch |  |  |  |  |  |  |  |
| Analog Signal Range ${ }^{\text {d }}$ | $\mathrm{v}_{\mathrm{NO}}, \mathrm{v}_{\mathrm{NC}}$, $\mathrm{V}_{\mathrm{COM}}$ |  | Full | 0 |  | V+ | V |
| On-Resistance | ron | $\mathrm{V}+=1.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=0.9 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=100 \mathrm{~mA}$ | Room Full |  | 0.8 | 2.0 2.5 | $\Omega$ |
| Switch Off Leakage Current ${ }^{f}$ | $\mathrm{I}_{\mathrm{NO} \text { (off), }}$ ${ }^{1} \mathrm{NC}$ (off) | $\begin{gathered} \mathrm{V}_{+}=2.2 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=0.2 \mathrm{~V} / 2.0 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=2.0 \mathrm{~V} / 0.2 \mathrm{~V} \end{gathered}$ | Room Fulld ${ }^{d}$ | $\begin{gathered} \hline-1 \\ -10 \end{gathered}$ |  | 1 10 | nA |
|  | ICom(off) |  | Room Fulld | $\begin{gathered} -1 \\ -10 \end{gathered}$ |  | 1 10 |  |
| Channel-On Leakage Current ${ }^{\dagger}$ | ${ }^{\text {com(on) }}$ | $\mathrm{V}_{+}=2.2 \mathrm{~V}, \mathrm{~V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{COM}}=0.2 \mathrm{~V} / 2.0 \mathrm{~V}$ | Room Fulld | $\begin{gathered} -1 \\ -10 \end{gathered}$ |  | $\begin{gathered} \hline 1 \\ 10 \end{gathered}$ |  |
| Digital Control |  |  |  |  |  |  |  |
| Input High Voltage | $\mathrm{V}_{\text {INH }}$ |  | Full | 1.0 |  |  |  |
| Input Low Voltage | $\mathrm{V}_{\text {INL }}$ |  | Full |  |  | 0.4 |  |
| Input Capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\text {in }}$ |  | Full |  | 5 |  | pF |
| Input Current ${ }^{\text {f }}$ | $\mathrm{l}_{\text {INL }}$ or $\mathrm{l}_{\text {INH }}$ | $\mathrm{V}_{\text {IN }}=0$ or $\mathrm{V}_{+}$ | Full | -1 |  | 1 | $\mu \mathrm{A}$ |
| Dynamic Characteristics |  |  |  |  |  |  |  |
| Turn-On Time ${ }^{\text {d }}$ | ton | $\mathrm{V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=\underset{\text { Figures } 1 \text { and 2 }}{1.5 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}}$ | Room Fulld |  | 36 | $\begin{aligned} & 60 \\ & 62 \end{aligned}$ | ns |
| Turn-Off Time ${ }^{\text {d }}$ | toff |  | $\begin{aligned} & \text { Room } \\ & \text { Fulld } \end{aligned}$ |  | 22 | $\begin{aligned} & 42 \\ & 44 \end{aligned}$ |  |
| Break-Before-Make Time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{d}}$ |  | Room | 3 |  |  |  |
| Charge Injectiond | Qinj | $\mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega$, Figure 3 | Room |  | 20 |  | pC |
| Off-Isolation ${ }^{\text {d }}$ | OIRR | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$ | Room |  | -56 |  | dB |
| Crosstalk ${ }^{\text {d }}$ | $\mathrm{X}_{\text {TALK }}$ |  | Room |  | -56 |  |  |
| NO, NC Off Capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\mathrm{NO} \text { (off), }}$ $\mathrm{C}_{\mathrm{NC} \text { (off) }}$ | $\mathrm{V}_{\mathrm{IN}}=0$ or $\mathrm{V}+\mathrm{f}=1 \mathrm{MHz}$ | Room |  | 73 |  | pF |
| Channel-On Capacitance ${ }^{\text {d }}$ | Con |  | Room |  | 167 |  |  |

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| SPECIFICATIONS (V+ = 3.0 V) |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Parameter | Symbol | Test Conditions Otherwise Unless Specified$\mathrm{V}_{+}=3 \mathrm{~V}, \pm 10 \%, \mathrm{~V}_{\mathrm{N}}=0.5 \text { or } 1.4 \mathrm{~V}$ | Temp ${ }^{\text {a }}$ | Limits-40 to $85^{\circ} \mathrm{C}$ |  |  | Unit |
|  |  |  |  | Min ${ }^{\text {b }}$ | Typ ${ }^{\text {c }}$ | Max ${ }^{\text {b }}$ |  |

## Analog Switch

| Analog Signal Range ${ }^{\text {d }}$ | $\mathrm{V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}$, $\mathrm{V}_{\mathrm{COM}}$ |  | Full | 0 |  | V+ | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| On-Resistance | ron | $\begin{gathered} \mathrm{V}+=2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=1.5 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}} \\ \mathrm{I}_{\mathrm{NC}}=100 \mathrm{~mA} \end{gathered}$ | Room Full |  | 0.44 | $\begin{aligned} & 0.6 \\ & 0.7 \end{aligned}$ | $\Omega$ |
| ron Flatness | ron Flatness | $\begin{gathered} \mathrm{V}+=2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=0.6 \mathrm{~V}, 1.5 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}} \\ \mathrm{I}_{\mathrm{NC}}=100 \mathrm{~mA} \end{gathered}$ | Room |  | 0.14 | 0.2 |  |
| ron Match | $\Delta r_{\text {ON }}$ | $\mathrm{V}+=2.7 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=1.5 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=100 \mathrm{~mA}$ | Room |  |  | 0.07 |  |
| Switch Off Leakage Current | $\mathrm{I}_{\mathrm{NO} \text { (off), }}$ ${ }^{1} \mathrm{NC}$ (off) | $\begin{gathered} \mathrm{V}_{+}=3.3 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=0.3 \mathrm{~V} / 3 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=3 \mathrm{~V} / 0.3 \mathrm{~V} \end{gathered}$ | Room Full | $\begin{gathered} \hline-1 \\ -10 \end{gathered}$ |  | $\begin{gathered} 1 \\ 10 \end{gathered}$ | nA |
|  | ICOM(off) |  | Room Full | $\begin{gathered} \hline-1 \\ -10 \end{gathered}$ |  | $\begin{gathered} 1 \\ 10 \end{gathered}$ |  |
| Channel-On Leakage Current | $\mathrm{I}_{\text {COM }}$ (on) | $\mathrm{V}+=3.3 \mathrm{~V}, \mathrm{~V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{COM}}=0.3 \mathrm{~V} / 3 \mathrm{~V}$ | Room Full | $\begin{gathered} \hline-1 \\ -10 \end{gathered}$ |  | $\begin{gathered} 1 \\ 10 \end{gathered}$ |  |
| Digital Control |  |  |  |  |  |  |  |
| Input High Voltage | $\mathrm{V}_{\text {INH }}$ |  | Full | 1.4 |  |  | V |
| Input Low Voltage | $V_{\text {INL }}$ |  | Full |  |  | 0.5 |  |
| Input Capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\text {in }}$ |  | Full |  | 5 |  | pF |
| Input Current ${ }^{\dagger}$ | $\mathrm{I}_{\text {INL }}$ or $\mathrm{I}_{\text {INH }}$ | $\mathrm{V}_{\text {IN }}=0$ or $\mathrm{V}+$ | Full | -1 |  | 1 | $\mu \mathrm{A}$ |

## Dynamic Characteristics

| Turn-On Time | ton | $\mathrm{V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=1.5 \mathrm{~V}, \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> Figure 1 and 2 | Room Full |  | 25 | $\begin{aligned} & 46 \\ & 48 \end{aligned}$ | ns |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Turn-Off Time | toff |  | Room Full |  | 14 | $\begin{aligned} & 38 \\ & 40 \end{aligned}$ |  |
| Break-Before-Make Time | $\mathrm{t}_{\mathrm{d}}$ |  | Room | 1 |  |  |  |
| Charge Injection ${ }^{\text {d }}$ | $\mathrm{Q}_{\text {INJ }}$ | $\mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega$, Figure 3 | Room |  | 28 |  | pC |
| Off-Isolation ${ }^{\text {d }}$ | OIRR | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$ | Room |  | -56 |  | dB |
| Crosstalk ${ }^{\text {d }}$ | $\mathrm{X}_{\text {TALK }}$ |  | Room |  | -56 |  |  |
| NO, NC Off Capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\mathrm{NO}}$ (off), $\mathrm{C}_{\mathrm{NC} \text { (off) }}$ | $\mathrm{V}_{\mathrm{IN}}=0$ or $\mathrm{V}_{+}, \mathrm{f}=1 \mathrm{MHz}$ | Room |  | 70 |  | pF |
| Channel-On Capacitance ${ }^{\text {d }}$ | $\mathrm{Con}^{\text {O }}$ |  | Room |  | 163 |  |  |

## Power Supply

| Power Supply Range | $\mathrm{V}_{+}$ |  | 1.6 |  | 3.6 |
| :--- | :---: | :---: | :---: | :---: | :---: |
| Power Supply Current | $\mathrm{I}+$ | $\mathrm{V}+=3.6 \mathrm{~V}, \mathrm{~V}_{\mathbb{I N}}=0$ or $\mathrm{V}+$ |  | 0.01 | 1.0 |

## Notes:

a. Room $=25^{\circ} \mathrm{C}$, Full $=$ as determined by the operating suffix.
b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
c. Typical values are for design aid only, not guaranteed nor subject to production testing.
d. Guarantee by design, nor subjected to production test.
e. $\quad \mathrm{V}_{\mathrm{IN}}=$ input voltage to perform proper function.
f. Guaranteed by 3-V leakage testing, not production tested.

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TYPICAL CHARACTERISTICS ( $25^{\circ} \mathrm{C}$ UNLESS NOTED)


Supply Current vs. Temperature


Leakage Current vs. Temperature

ron vs. Analog Voltage and Temperature


VCOM - Analog Voltage (V)
Supply Current vs. Input Switching Frequency


Leakage vs. Analog Voltage


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## TYPICAL CHARACTERISTICS (25 ${ }^{\circ}$ C UNLESS NOTED)




Insertion Loss, Off-Isolation, Crosstalk vs. Frequency





Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

FIGURE 1. Switching Time


FIGURE 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

FIGURE 3. Charge Injection


FIGURE 4. Off-Isolation


FIGURE 5. Channel Off/On Capacitance

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